

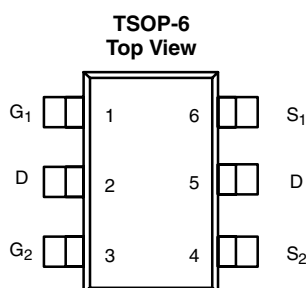
Complementary MOSFET Half-Bridge (N- and P-Channel)

PRODUCT SUMMARY

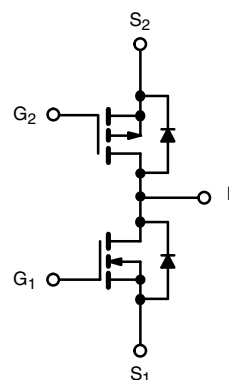
	V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
N-Channel	20	0.300 at $V_{GS} = 4.5$ V	1.4
		0.410 at $V_{GS} = 3.0$ V	1.2
P-Channel	- 20	0.640 at $V_{GS} = - 4.5$ V	- 0.96
		0.980 at $V_{GS} = - 3.0$ V	- 0.78

FEATURES

- 100 % R_g Tested


RoHS
COMPLIANT


Ordering Information: Si3850ADV-T1-E3 (Lead (Pb)-free)



ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

ABSOLUTE MAXIMUM RATINGS					
T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage	V _{DS}	20	- 20	V	
Gate-Source Voltage	V _{GS}	± 12			
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	1.4	- 0.96	A
	T _A = 70 °C		1.1	- 0.77	
Pulsed Drain Current		I _{DM}	3.5	- 2.0	
Continuous Source Current (Diode Conduction) ^a		I _S	0.9	- 0.9	
Maximum Power Dissipation (Surface Mounted on FR4 Board)	T _A = 25 °C	P _D	1.08		W
	T _A = 70 °C		0.70		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	N- or P-Channel	Unit
Maximum Junction-to-Ambient (Surface Mounted on FR4 Board, $\pm \leq 10$ sec)	R_{thJA}	115	°C/W

Notes:

Maximum under Steady State condition is 150 °C/W.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit	
Static								
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	0.6		1.5	V	
		V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 0.6		- 1.5		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V				± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V	N-Ch			1	μA	
		V _{DS} = - 20 V, V _{GS} = 0 V	P-Ch			- 1		
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 70 °C	N-Ch			10		
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 70 °C	P-Ch			- 10		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 4.5 V	N-Ch	3.0			A	
		V _{DS} = - 5 V, V _{GS} = - 4.5 V	P-Ch	- 1.5				
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 4.5 V, I _D = 0.5 A	N-Ch		0.240	0.300	Ω	
		V _{GS} = - 4.5 V, I _D = - 0.5 A	P-Ch		0.510	0.640		
		V _{GS} = 3.0 V, I _D = 0.5 A	N-Ch		0.325	0.410		
		V _{GS} = - 3.0 V, I _D = - 0.5 A	P-Ch		0.780	0.980		
Forward Transconductance ^b	g _{fs}	V _{DS} = 10 V, I _D = 1 A	N-Ch		1.8		S	
		V _{DS} = - 10 V, I _D = - 1 A	P-Ch		1.1			
Diode Forward Voltage ^b	V _{SD}	I _S = 0.9 A, V _{GS} = 0 V	N-Ch		0.87	1.2	V	
		I _S = - 0.8 A, V _{GS} = 0 V	P-Ch		- 1.0	- 1.3		
Dynamic ^b								
Total Gate Charge	Q _g	N-Channel V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 1 A	N-Ch		0.95	1.4	nC	
Gate-Source Charge	Q _{gs}		P-Ch		1.10	1.7		
		Gate-Drain Charge	Q _{gd}	P-Channel V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 1 A		N-Ch		
P-Ch				0.28				
Gate Resistance	R _g		N-Ch		0.24		Ω	
			P-Ch		0.26			
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 10 V, R _L = 10 Ω I _D ≅ 0.9 A, V _{GEN} = 4.5 V, R _G = 1 Ω	N-Ch		3.5	5.3		
Rise Time	t _r		P-Ch		10.5	16		
		Turn-Off Delay Time	t _{d(off)}	P-Channel V _{DD} = - 10 V, R _L = 10 Ω		N-Ch		8
P-Ch				13	20			
Fall Time	t _f	I _D ≅ - 0.9 A, V _{GEN} = - 4.5 V, R _G = 1 Ω	N-Ch		16	25		
			P-Ch		34	50		
Body Diode Reverse Recovery Tme	t _{rr}		N-Ch		20	30		
			P-Ch		18	30		
Body Diode Reverse Recovery Charge	Q _{rr}		N-Ch		9	15	nC	
			P-Ch		18	30		

Notes:

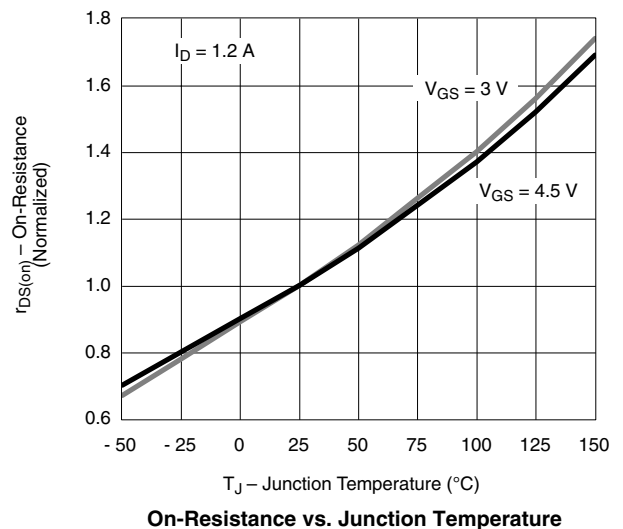
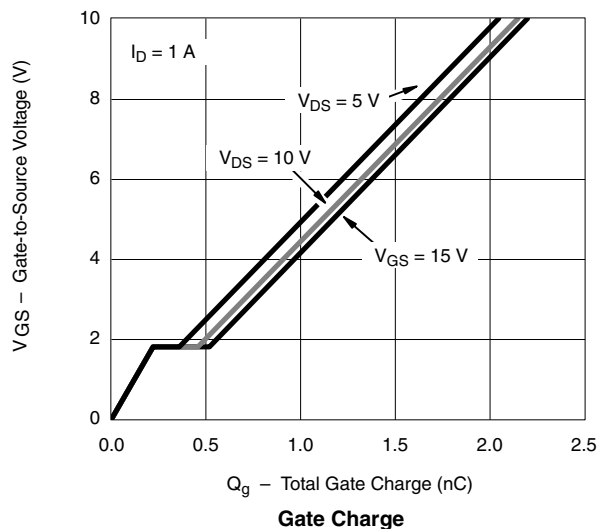
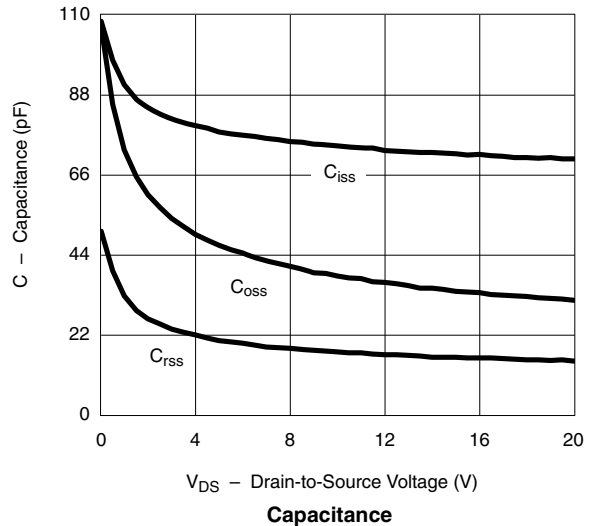
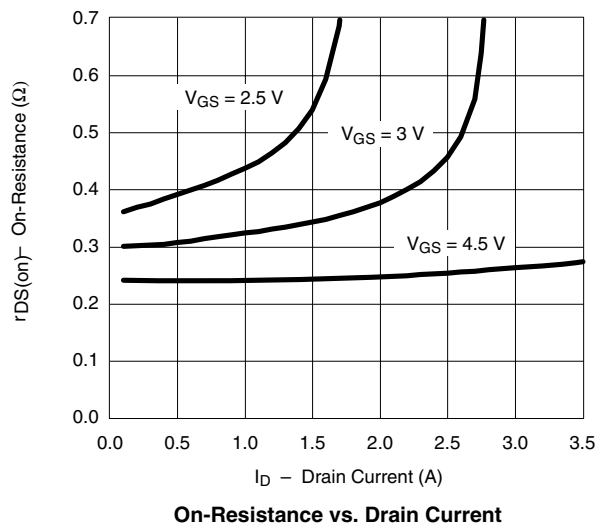
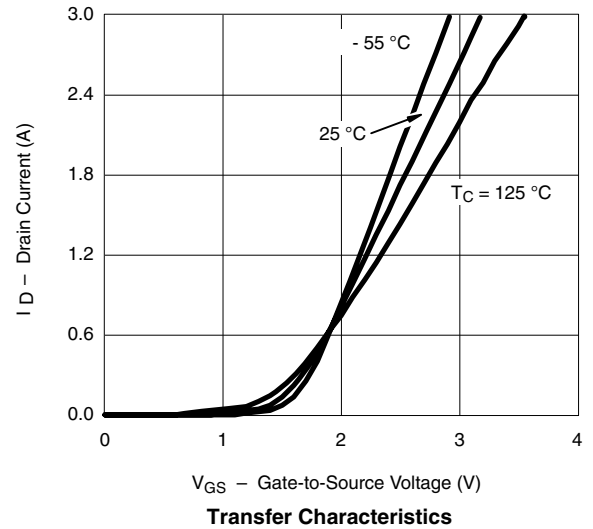
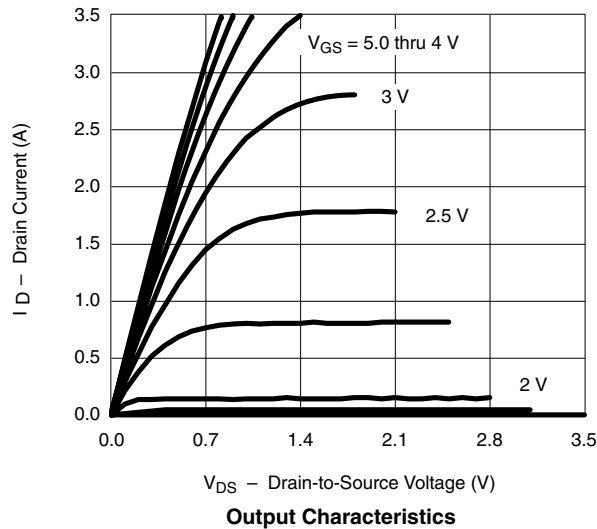
a. Guaranteed by design, not subject to production testing.

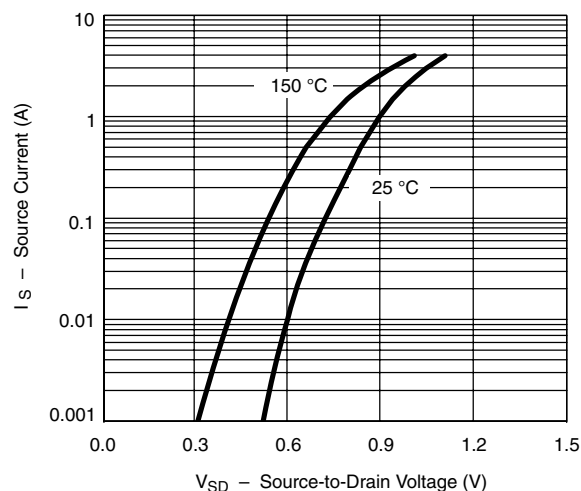
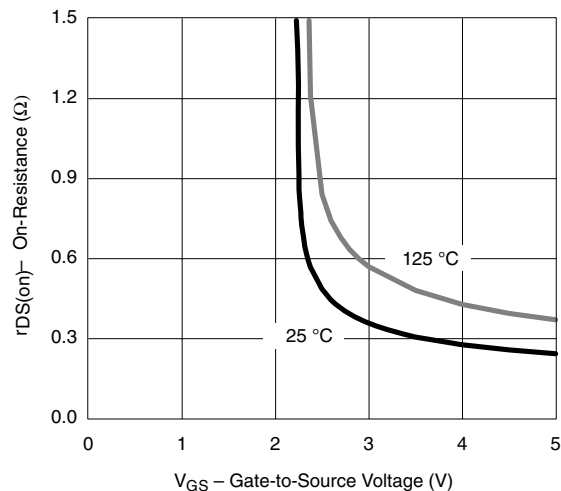
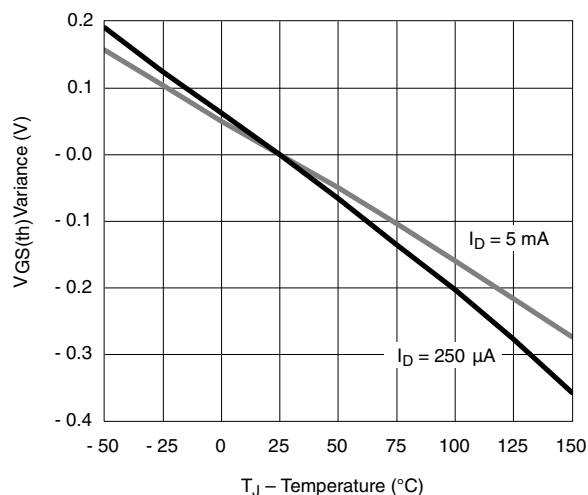
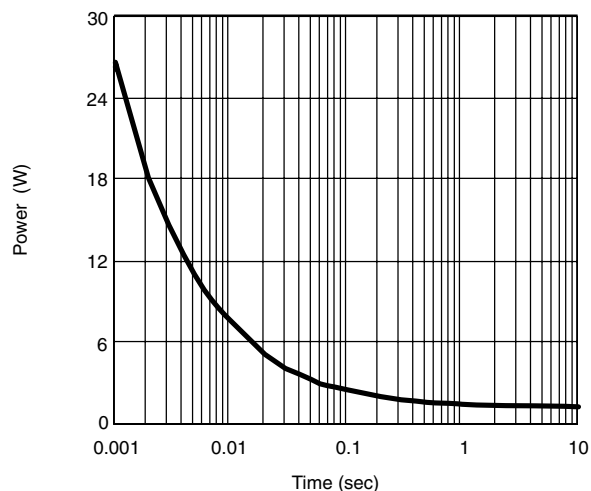
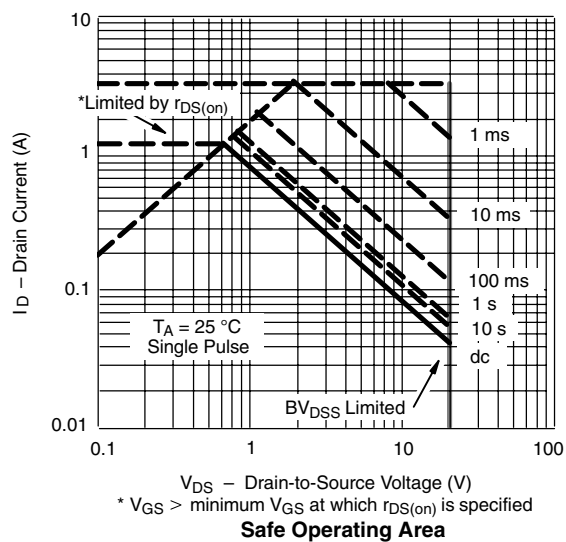
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

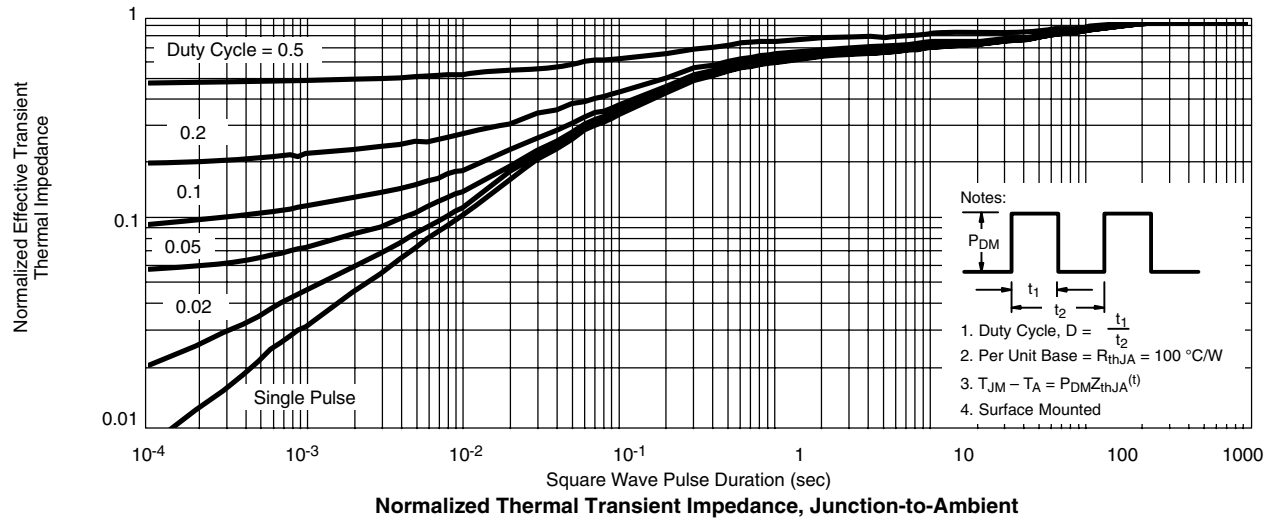


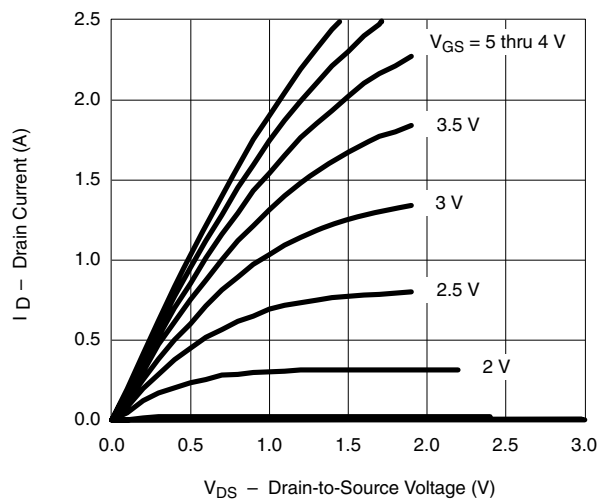
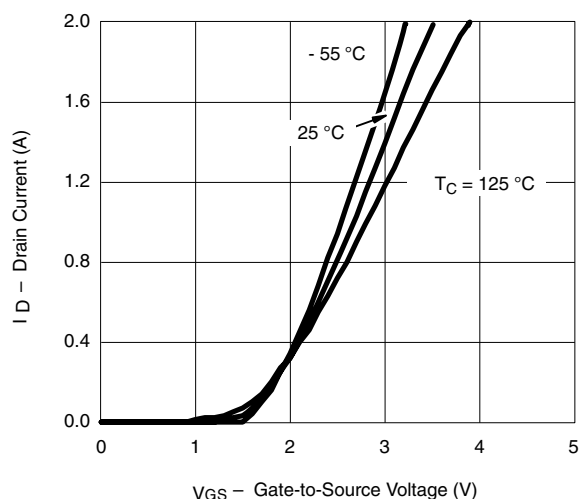
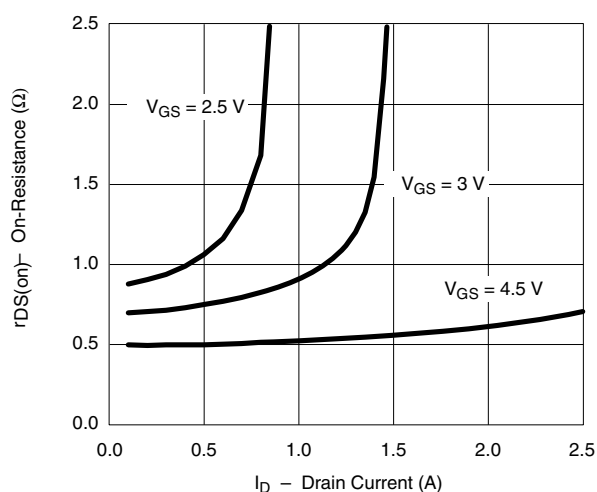
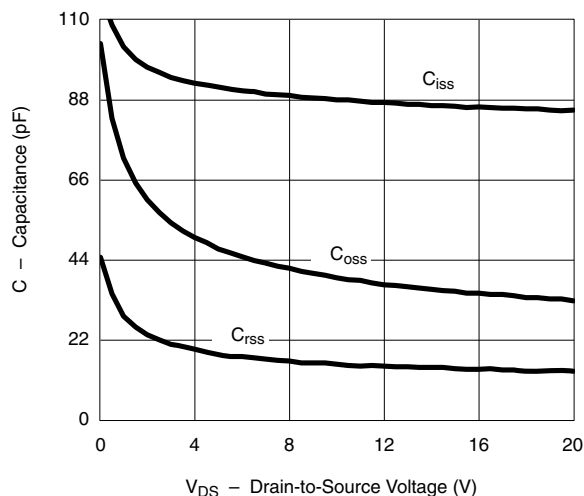
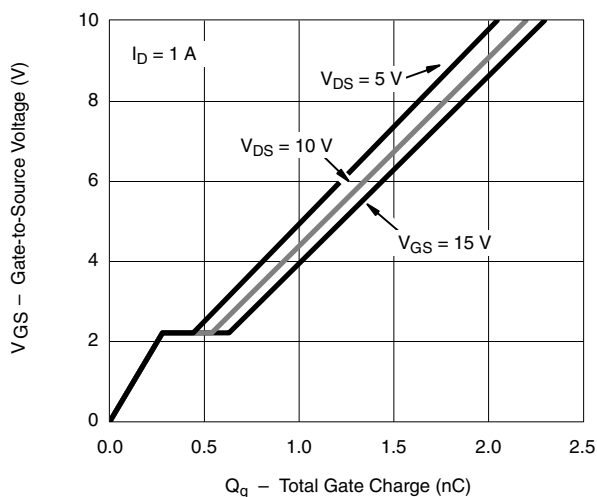
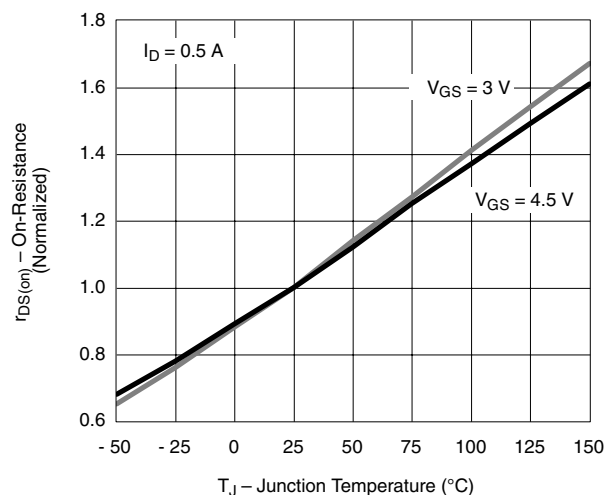
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted



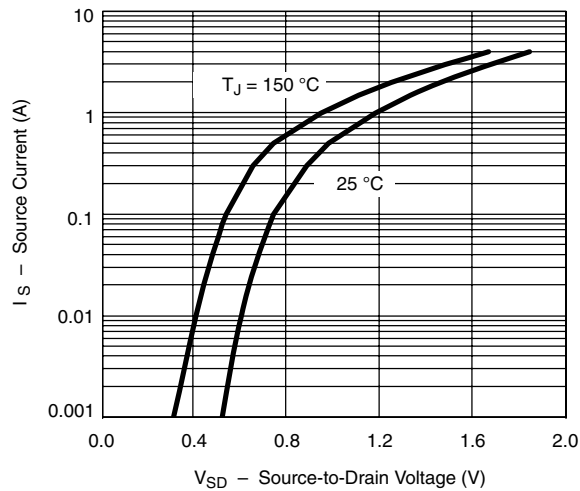
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power****Safe Operating Area**

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted

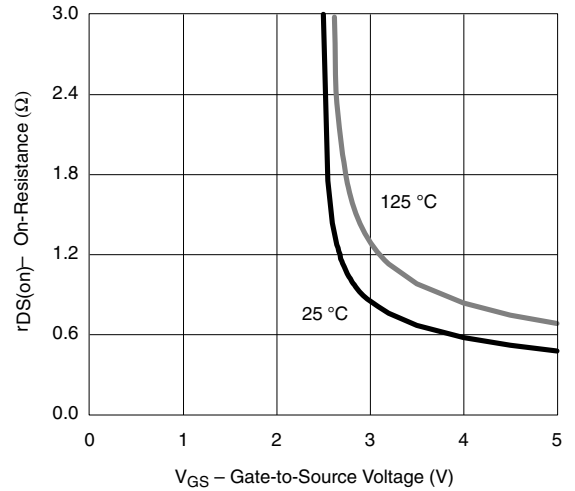


P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

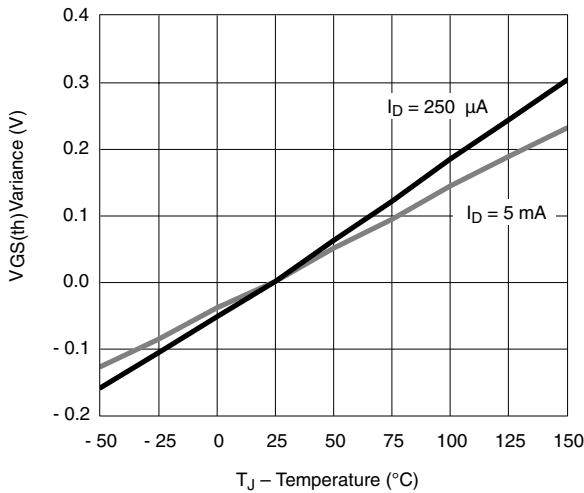
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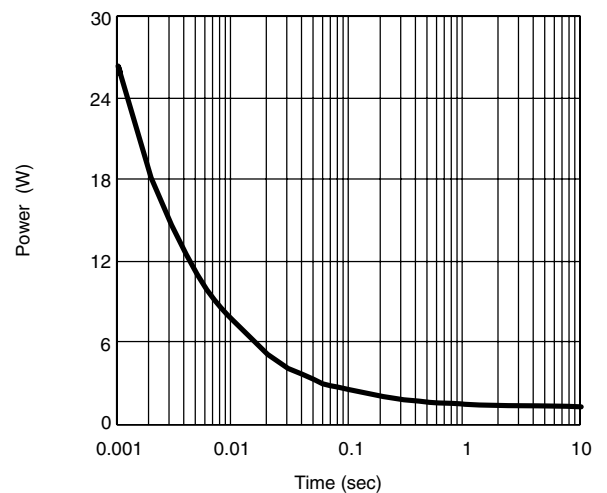
Source-Drain Diode Forward Voltage



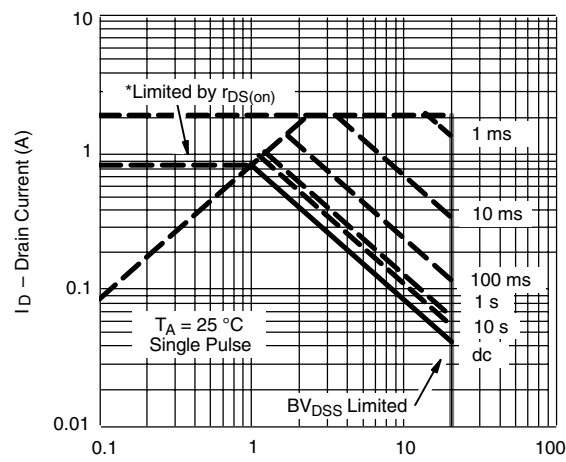
On-Resistance vs. Gate-to-Source Voltage



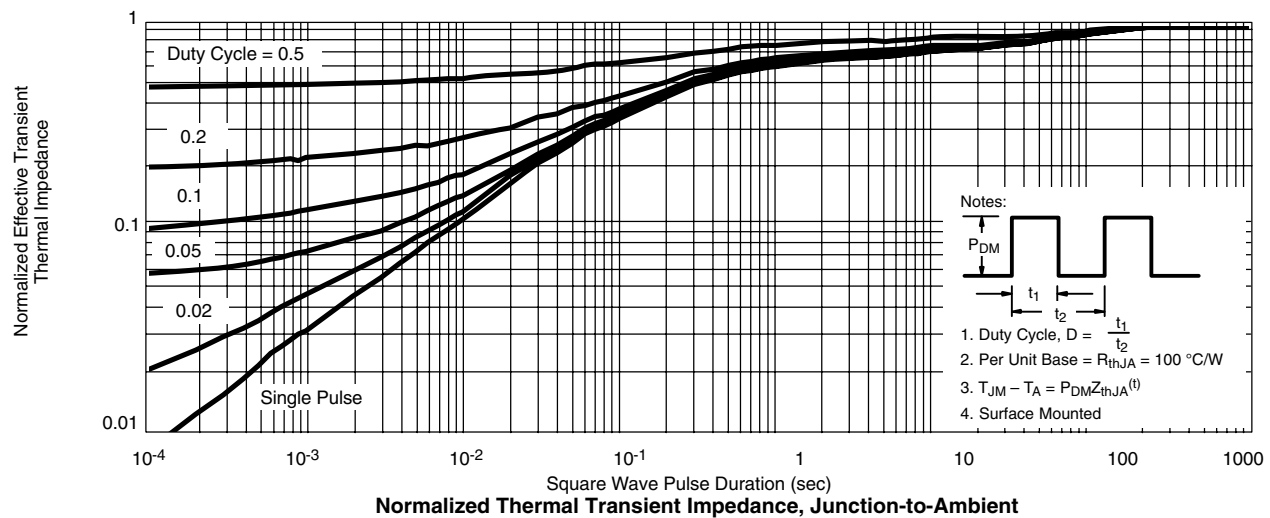
Threshold Voltage



Single Pulse Power vs. Junction-to-Ambient



Safe Operating Area

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted

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